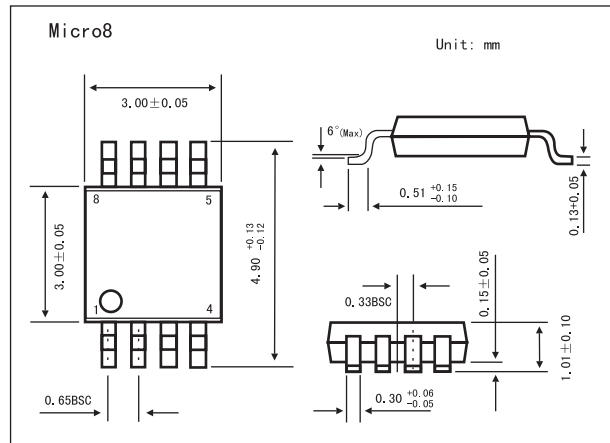
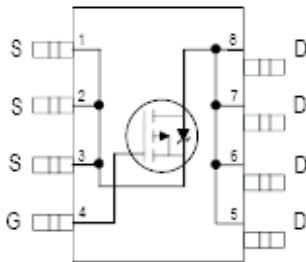


HEXFET[®] Power MOSFET

KRF7604

■ Features

- Ultra Low On-Resistance
- P-Channel MOSFET
- Very Small SOIC Package
- Low Profile (< 1.1mm)
- Available in Tape & Reel
- Fast Switching



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Continuous Drain Current, V _{GS} @ -4.5V @ Ta = 25°C	I _D	-3.6	A
Continuous Drain Current, V _{GS} @ -4.5V @ Ta = 70°C	I _D	-2.9	
Pulsed Drain Current *1	I _{DM}	-19	
Power Dissipation @Ta= 25°C	P _D	1.8	W
Linear Derating Factor		14	mW/°C
Gate-to-Source Voltage	V _{GS}	± 12	V
Peak Diode Recovery dv/dt *2	dv/dt	-5.0	V/ns
Junction and Storage Temperature Range	T _J , T _{STG}	-55 to + 150	°C
Maximum Junction-to-Ambient *3	R _{θJA}	70	°C/W


*1 Repetitive rating; pulse width limited by max. junction temperature.

*2 I_{SD} ≤ -2.4A, di/dt ≤ -96A/μs, V_{DD} ≤ V_{(BR)DSS}, T_J ≤ 150°C

*3 Surface mounted on FR-4 board, t ≤ 10sec.

KRF7604

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -250 \mu A$	-20			V
Breakdown Voltage Temp. Coefficient	$\Delta V_{(BR)DSS} / \Delta T_J$	$I_D = -1mA, \text{Reference to } 25^\circ C$		-0.022		V/°C
Static Drain-to-Source On-Resistance	$R_{DS(on)}$	$V_{GS} = -4.5V, I_D = -2.4A^{*1}$			0.09	mΩ
		$V_{GS} = -2.7V, I_D = -1.2A^{*1}$			0.13	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250 \mu A$	-0.70			V
Forward Transconductance	g_{fs}	$V_{DS} = -10V, I_D = -1.2A^{*1}$	2.6			S
Drain-to-Source Leakage Current	I_{DSS}	$V_{DS} = -16V, V_{GS} = 0V$			-1.0	μA
		$V_{DS} = -16V, V_{GS} = 0V, T_J = 125^\circ C$			-25	
Gate-to-Source Forward Leakage	I_{GSS}	$V_{GS} = -12V$			-100	nA
Gate-to-Source Reverse Leakage		$V_{GS} = 12V$			100	
Total Gate Charge	Q_g	$I_D = -2.4A$		13	20	nC
Gate-to-Source Charge	Q_{gs}	$V_{DS} = -16V$		2.6	3.9	
Gate-to-Drain ("Miller") Charge	Q_{gd}	$V_{GS} = -4.5V$		5.6	9.0	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -10V$		17		ns
Rise Time	t_r	$I_D = -2.4A$		53		
Turn-Off Delay Time	$t_{d(off)}$	$R_G = 6 \Omega$		31		
Fall Time	t_f	$R_D = 4.0 \Omega$		38		
Input Capacitance	C_{iss}	$V_{GS} = 0V$		590		pF
Output Capacitance	C_{oss}	$V_{DS} = -15V$		330		
Reverse Transfer Capacitance	C_{rss}	$f = 1.0MHz$		170		
Continuous Source Current (Body Diode)	I_S	MOSFET symbol showing the integral reverse p-n junction diode. 			-1.8	A
Pulsed Source Current (Body Diode) *2	I_{SM}				-19	
Diode Forward Voltage	V_{SD}	$T_J = 25^\circ C, I_S = -2.4A, V_{GS} = 0V^{*1}$			-1.2	V
Reverse Recovery Time	t_{rr}	$T_J = 25^\circ C, I_F = -2.4A$		41	62	ns
Reverse Recovery Charge	Q_{rr}	$di/dt = 100A / \mu s^{*1}$		38	57	μC

*1 Pulse width $\leq 300 \mu s$; duty cycle $\leq 2\%$.

*2 Repetitive rating; pulse width limited by max. junction temperature.